

***EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 809; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.**

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Multiple sheets used when necessary)

APR 25 2005

SHEET 1 OF 1

Application No.	10/800,390
Filing Date	March 12, 2004
First Named Inventor	Paul D. Brabant
Art Unit	2818
Examiner	David Vu
Attorney Docket No.	ASMEX.448A

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
DV	1	2003/0045063	03/06/2003	Oda	
DV	2	2003/0082300	05/01/2003	Todd et al.	
DV	3	2003/0124818	07/03/2003	Luo et al.	
DV	4	2005/0079692	04/14/2005	Samoilov et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T ¹
DV	5	WO 00/15885	03/23/2000	Hernandez et al.		

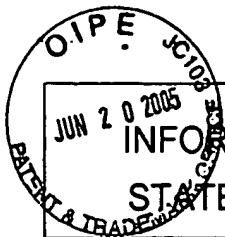
NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
DV	6	International Search Report for International Application No. PCT/US04/07564 dated April 6, 2005.	

1678010:042105

Examiner Signature <i>Shulard</i>	Date Considered <i>03/03/05</i>
<p>*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>	

T¹ - Place a check mark in this area when an English language Translation is attached.



PTO/SB/08 Equivalent

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Multiple sheets used when necessary) SHEET 1 OF 1	Application No.	10/800,390
	Filing Date	March 12, 2004
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DV	1.	2005/0079692	04/14/2005	Samoilov et al.	

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMEX.448AAPPLICATION NO.
10/800,390INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Brabant et al.FILING DATE
March 12, 2004GROUP
Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	1	US 2003/0235931 A1	12/25/03	Wada et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)		
DV	2	Cannon, D. et al., "Tensile strained epitaxial Ge films on Si(100) substrates with potential application in L-band telecommunications," Applied Physics Letters, Volume 84, Number 6, February 9, 2004, pp. 906-908.	
	3	Colace, L. et al., "Efficient high-speed near-infrared Ge photodetectors integrated on Si substrates," Applied Physics Letters, Volume 76, Number 10, March 6, 2000, pp. 1231-1233.	
	4	Colace, L. et al., "Ge-on-Si Approaches to the Detection of Near-Infrared Light," IEEE Journal of Quantum Electronics, Vol. 35, No. 12, December 1999, pp. 1843-1852.	
	5	Fama, S. et al., "High performance germanium-on-silicon detectors for optical communications," Applied Physics Letters, Volume 81, Number 4, July 22, 2002, pp. 586-588..	
	6	Hull, R., "Metastable strained layer configurations in the SiGe/Si system," (1999) EMIS Datareviews, Series No. 24: Properties of SiGe and SiGe:C, edited by Erich Kasper et al., INSPEC (2000), London, UK	
	7	Ishikawa, Y. et al., "Strain-induced band gap shrinkage in Ge grown on Si substrate," Applied Physics Letters, Volume 82, Number 12, March 31, 2003, pp. 2044-2046.	
	8	Lee et al., "Growth of strained Si and strained Ge heterostructures on relaxed Si _{1-x} G _x by ultrahigh vacuum chemical vapor deposition," J. Vac. Sci. Technol. B 22(1) (Jan/Feb 2004).	
	9	Li, Q, et al., "Selective growth of Ge on Si(100) through vias of SiO ₂ nanotemplate using solid source molecular beam epitaxy," Applied Physics Letters, Volume 83, Number 24, December 15, 2003, pp. 5032-5034.	
DV	10	Liu, J. et al., "Silicidation -induced band gap shrinkage in Ge epitaxial films on Si," Applied Physics Letters, Volume 84, Number 5, February 2, 2004, pp. 660-662.	

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. ASMEX.448A	APPLICATION NO. 10/800,390
	APPLICANT Brabant et al.	
	FILING DATE March 12, 2004	GROUP Unknown

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
DV	11 Masini, G. et al.; "High-Performance p-i-n Ge on Si Photodetectors for the Near Infrared: From Model to Demonstration," IEEE Transactions of Electron Devices, Vol. 48, No. 6, June 2001, pp. 1092-1096.
DV	12 Schollhorn et al., "Coalescence of germanium islands on silicon," Thin Solid Films," Vol. 336 (1988), pp. 109-111.

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